

# **isc Silicon NPN Darlington Power Transistor**

BUX90

### **DESCRIPTION**

- Collector-Emitter Sustaining Voltage-V<sub>CEO(SUS)</sub>= 400V(Min)
- · High Reliability
- DARLINGTON
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**



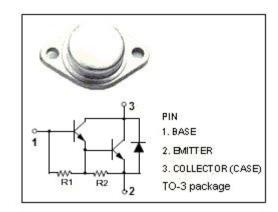
- · Automotive ignition applications
- · Inverters circuits for motor controls

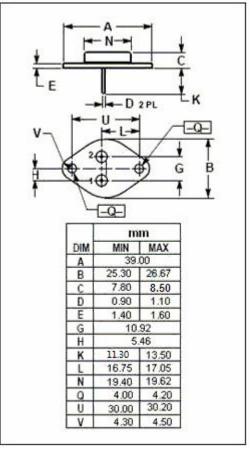
ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>СВО</sub>	Collector-Base Voltage	650	V
V <sub>CEO</sub>	Collector-Emitter Voltage	400	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
Ic	Collector Current	12	Α
I <sub>CM</sub>	Collector Current-peak	20	Α
I <sub>B</sub>	Base Current	1	Α
Івм	Base Current-peak	5	Α
Pc	Collector Power Dissipation @T <sub>C</sub> =25°C	125	W
Tj	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$ C

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT		
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	1.0	°C/W		







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#### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>B</sub> = 0	400			V
V <sub>CE</sub> (sat)-1	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 100mA			1.6	V
V <sub>CE</sub> (sat) -2	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 250mA			1.8	V
V BE(sat) -1	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A; I <sub>B</sub> = 100mA			2.2	V
V BE(sat) -2	Base-Emitter Saturation Voltage	I <sub>C</sub> = 10A; I <sub>B</sub> = 250mA			2.5	V
I <sub>CES</sub>	Collector Cutoff Current	V <sub>CE</sub> = 650V;V <sub>BE</sub> = 0 V <sub>CE</sub> = 650V;V <sub>BE</sub> = 0;T <sub>j</sub> = 125℃			1.0 5.0	mA
I <sub>CEO</sub>	Collector Cutoff Current	V <sub>CE</sub> = 400V;I <sub>B</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			20	mA
h <sub>FE</sub>	DC Current Gain	Ic= 5A; Vc== 10V	300			
V <sub>ECF</sub>	C-E Diode Forward Voltage	I <sub>F</sub> = 10A			2.8	V

## **NOTICE:**

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